

# Method for Transistor Gate Dielectric Layer with Uniform Nitrogen Concentration

## 5 ABSTRACT OF THE INVENTION

The instant invention describes a method for forming a dielectric film with a uniform concentration of nitrogen. The films are formed by first incorporating nitrogen into a dielectric film using RPNO. The films are then annealed in  
10 N<sub>2</sub>O which redistributes the incorporated species to produce a uniform nitrogen concentration.

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